

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current, V _{GS} = 10V (Note 7)	Steady State	$T_C = +25$ °C $T_C = +70$ °C	Ι _D	60 45	А
Maximum Body Diode Forward Current (Note 7)			Is	2	Α
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)			I _{DM}	90	Α
Pulsed Drain Body Diode Forward Current (380µs Pulse, Duty Cycle = 1%)			I _{SM}	90	А
Avalanche Current (L = 0.1mH) (Note 8)			I _{AS}	24	Α
Avalanche Energy (L = 0.1mH) (Note 8)			E _{AS}	29	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_{D}	1.0	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	130	°C/W
Total Power Dissipation (Note 6)		P_{D}	2.0	W
Thermal Resistance, Junction to Ambient (Note 6) Steady State		$R_{ heta JA}$	63	°C/W
Thermal Resistance, Junction to Case (Note 7)		$R_{ heta JC}$	2.9	C/VV
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

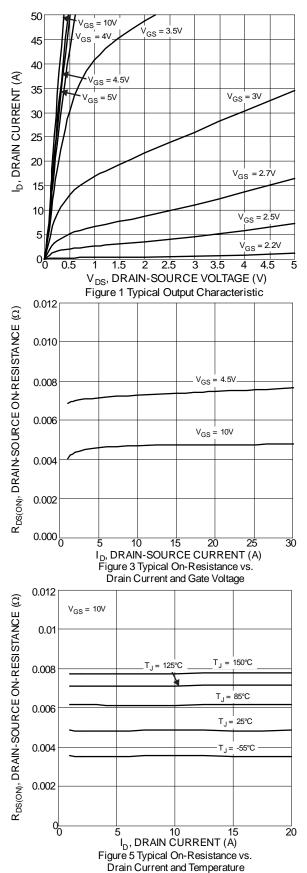
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}		_	1	μΑ	$V_{DS} = 24V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	_	±100	nA	$V_{GS} = +20V, V_{DS} = 0V$ $V_{GS} = -16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	1.0	_	3.0	٧	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance			5.6	7	mΩ	$V_{GS} = 10V, I_D = 9.0A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	8.0	11		$V_{GS} = 4.5V, I_D = 8.5A$	
Diode Forward Voltage	V_{SD}	_	0.70	1.2	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	_	1,155			$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz	
Output Capacitance	Coss	_	456	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	72	_			
Gate Resistance	R_g	_	1.6	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1.0MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	8.4	_			
Total Gate Charge (V _{GS} = 10V)	Q_g	_	16.7	_	nC	V _{DD} = 15V, I _D = 9A	
Gate-Source Charge	Qgs	_	2.2	_	nc		
Gate-Drain Charge	Q_{gd}	_	3.5	_			
Turn-On Delay Time	t _{D(ON)}	_	3.5	_		$V_{DD} = 15V, V_{GS} = 10V,$ $R_g = 3\Omega, I_D = 9A$	
Turn-On Rise Time	t _R	_	5.5	_			
Turn-Off Delay Time	t _{D(OFF)}	_	13.5	_	ns		
Turn-Off Fall Time	t _F	_	4.6	_			
Reverse Recovery Time	t _{RR}	_	19.3	_	ns	1 4 5 4 3 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4 4	
Reverse Recovery Charge	Q _{RR}		8.6	_	nC	$I_F = 1.5A$, di/dt = 100A/ μ s	

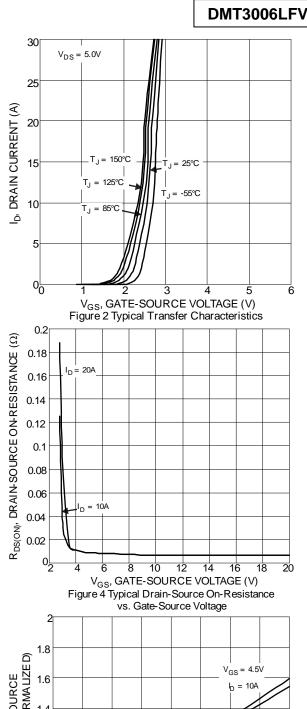
Notes:

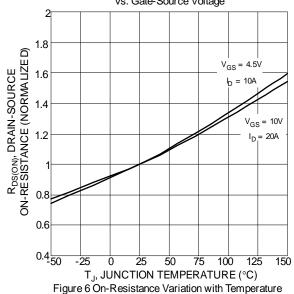
- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.



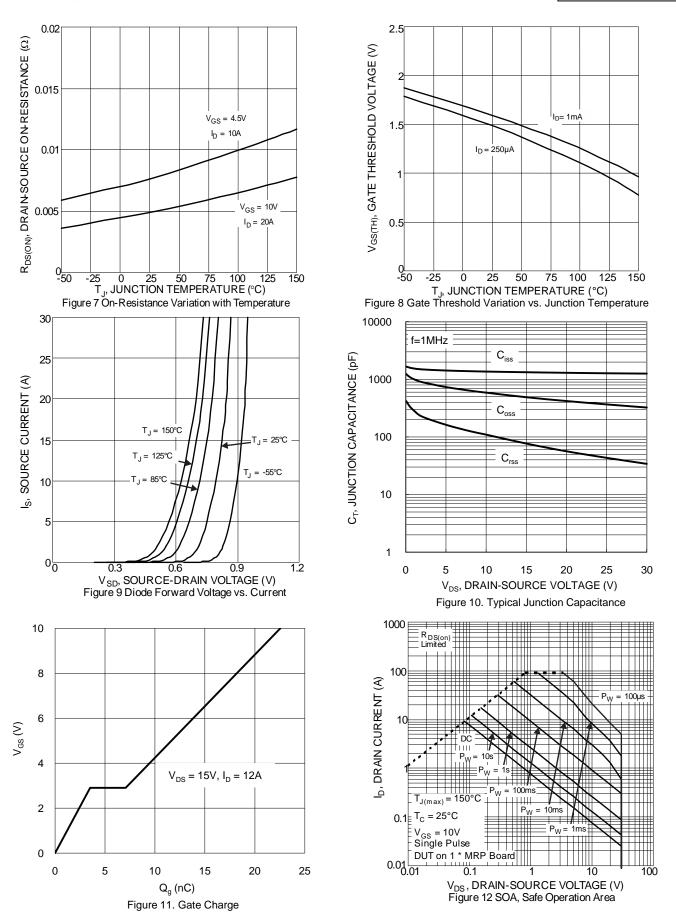




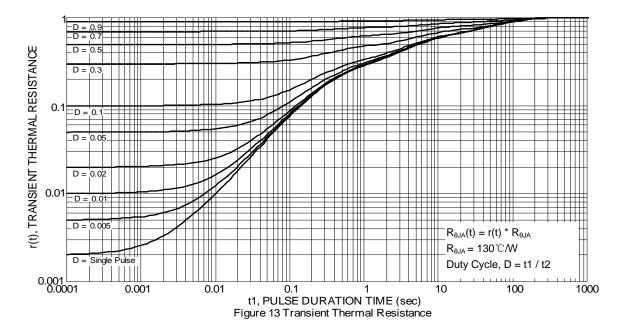










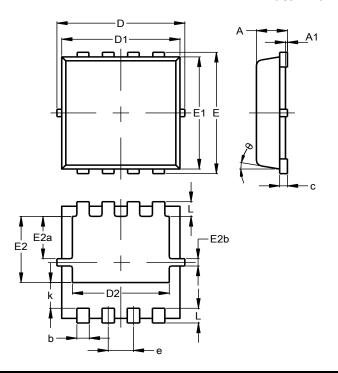




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)

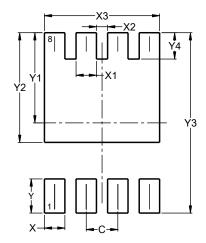


PowerDI3333-8 (Type UX)					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05			
b	0.25	0.40	0.32		
С	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	2.30	2.70	2.50		
Е	3.20	3.40	3.30		
E1	2.95	3.15	3.05		
E2	1.60	2.00	1.80		
E2a	0.95	1.35	1.15		
E2b	0.10	0.30	0.20		
е	0.65 BSC				
k	0.50	0.90	0.70		
L	0.30	0.50	0.40		
θ	0°	12°	10°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)



Dimensions	Value (in mm)
С	0.650
X	0.420
X1	0.420
X2	0.230
Х3	2.370
Υ	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540



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